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Kind regards,

Team Nexperia



PMBTA42DS

NPN/NPN high-voltage double transistors Rev. 02 — 27 August 2009

Product data sheet

Product profile

1.1 General description

NPN/NPN high-voltage double transistors in a small SOT457 (SC-74) Surface Mounted Device (SMD) plastic package.

1.2 Features

- High breakdown voltage
- Two electrically isolated transistors
- Small SMD plastic package

1.3 Applications

- Automotive:
 - High- and low-side switches
 - Voltage regulators
- Communication: Telecom line interface
- Consumer: CRT TV Computing: Monitors

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or					
V_{CEO}	collector-emitter voltage	open base	-	-	300	V
I _C	collector current		-	-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	200	mA



2. Pinning information

Table 2. Pinning

i iiiiiiig		
Description	Simplified outline	Symbol
emitter TR1	D. D. D.	
base TR2	<u> 6 5 4</u>	6 5 4
collector TR2		
emitter TR2	1 12 13	TR1 TR2
base TR1		
collector TR1		
	Description emitter TR1 base TR2 collector TR2 emitter TR2 base TR1	Description emitter TR1 base TR2 collector TR2 emitter TR2 base TR1

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMBTA42DS	SC-74	plastic surface mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 4. Marking codes

Type number	Marking code
PMBTA42DS	P4

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	300	V
V_{CEO}	collector-emitter voltage	open base	-	300	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	200	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u> _	290	mW
			[2] _	370	mW
			[3]	450	mW

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NPN/NPN high-voltage double transistors

Limiting values ...continued Table 5.

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	420	mW
			[2] _	560	mW
			[3] _	700	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard

Thermal characteristics 6.

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
R _{th(j-a)}	thermal resistance from	in free air	<u>[1]</u> _	-	431	K/W
	junction to ambient		[2] _	-	338	K/W
			[3] _	-	278	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	105	K/W
Per devic	е					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	298	K/W
			[2] _	-	223	K/W
			[3] _	-	179	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1cm².

^[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1cm².

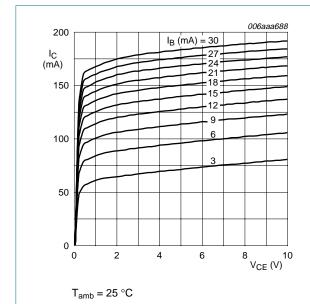
^[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

Characteristics 7.

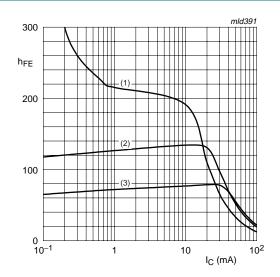
Table 7. **Characteristics**

T_{amb} = 25 °C unless otherwise specified

mb – 23 O diffessional diffessi						
nbol i	Parameter	Conditions	Min	Тур	Max	Unit
transis	stor					
•	collector-base cut-off current	$V_{CB} = 200 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
•	emitter-base cut-off current	$V_{EB} = 6 \text{ V}; I_C = 0 \text{ A}$	-	-	100	nA
h _{FE} D	DC current gain	$V_{CE} = 10 \text{ V}; I_{C} = 1 \text{ mA}$	25	-	-	
		$V_{CE} = 10 \text{ V}; I_{C} = 10 \text{ mA}$	40	-	-	
		$V_{CE} = 10 \text{ V}; I_{C} = 30 \text{ mA}$	40	-	-	
_501	collector-emitter saturation voltage	$I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$	-	-	500	mV
-501	base-emitter saturation voltage	$I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$	-	-	900	mV
	feedback capacitance	$V_{CB} = 20 \text{ V}; I_C = I_c = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
	transition frequency	$V_{CE} = 20 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	50	-	-	MHz
			50	-	-	



Collector current as a function of Fig 1. collector-emitter voltage; typical values



 $V_{CE} = 10 \text{ V}$

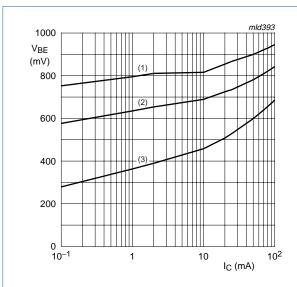
(1) $T_{amb} = 150 \,^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

DC current gain as a function of collector Fig 2. current; typical values

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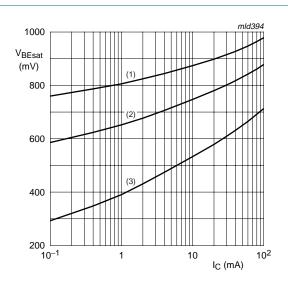
$$V_{CE} = 10 \text{ V}$$

(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 3. Base-emitter voltage as a function of collector current; typical values



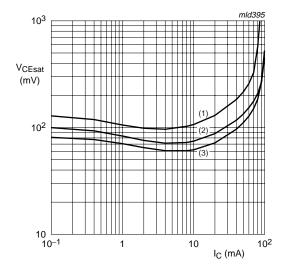
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 4. Base-emitter saturation voltage as a function of collector current, typical values



$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

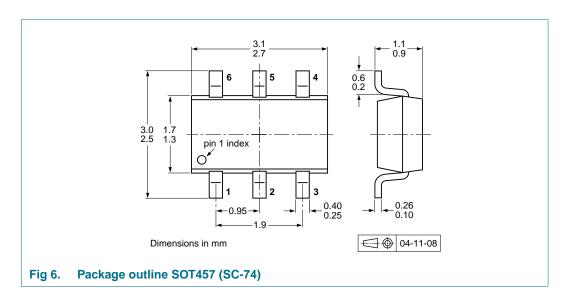
(3) $T_{amb} = -55 \,^{\circ}C$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values

Product data sheet

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8. Package outline



9. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

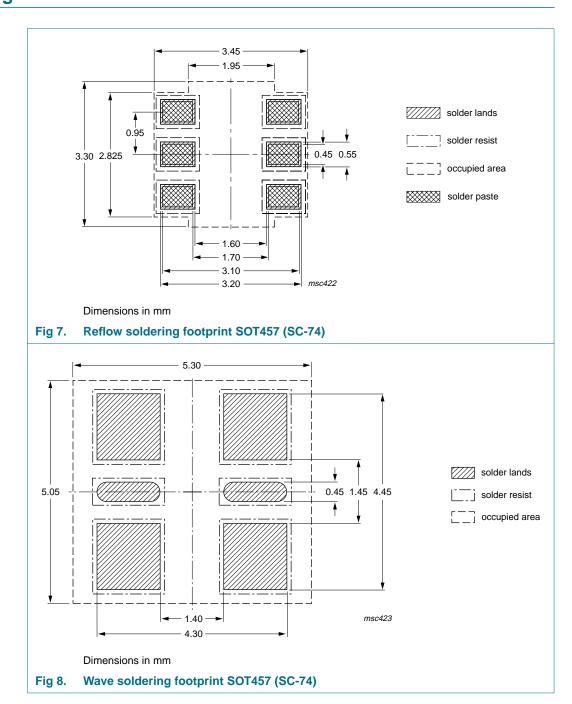
Type number	Package	Description		Packing qua	intity
				3000	10000
PMBTA42DS SOT457 4 i		4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165

^[1] For further information and the availability of packing methods, see $\underline{\text{Section 13}}$.

[2] T1: normal taping

[3] T2: reverse taping

10. Soldering





11. Revision history

Table 9. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBTA42DS_2	20090827	Product data sheet	-	PMBTA42DS_1
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 			
	Figure 8 "Wa	ave soldering footprint SOT	<u>457 (SC-74)"</u> :updated	1
PMBTA42DS_1	20060106	Product data sheet	-	-

12. Legal information

12.1 **Data sheet status**

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- The term 'short data sheet' is explained in section "Definitions"
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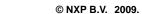
PMBTA42DS

NPN/NPN high-voltage double transistors

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